

ELE 3510 Lab 1: RC Circuits

2 dedicated lab periods, 2 lab periods to complete

Objectives

- Review MultiSim schematic entry and simulation
- Review timing calculations
- Review power calculations

Prelab

- [Setup](#) MultiSim using the MultiSim Setup slides

student
check off

In lab Activities – MSOE Library Setup (do not do this on your own)

- [Setup](#) the MSOE MultiSim Template
- [Setup](#) the MSOE 45nm MOSFET Library

check off

Assignment

Part 1: RC time constants and simulation measurements

- 1) Using the circuits from the Part 1 Schematic – **calculate** the expected delay times t_{pdr} , t_{pdf} , and the expected rise and fall times t_r , t_f ([This requires you to use equations](#))
These measurements are defined in the Common Waveform Measurements slides
- 2) [Create](#) the Part 1 Schematic in MultiSim
(be sure to put it in your personal MultiSim project directory)
- 3) Using the circuits from the Part 1 Schematic – [simulate and measure](#) the delay times t_{pdr} , t_{pdf} , and the rise and fall times t_r , t_f
- 4) [Compare](#) your calculations to the simulated results
- 5) [Discuss](#) the impact of output impedance (the R) and the load capacitance (the C) on these results

Part 2: CMOS Inverter Current

- 1) [Create](#) the Part 2 Schematic in MultiSim
Carefully note the direction of the MOSFETs
- 2) Perform the simulations a-g as outlined in the Part 2 appendix
- 3) Provide explanations for each plot and answer the questions in red.

Check Off

[You must demonstrate 1 working simulation from each part prior to the beginning of the lab following the second lab \(all simulations should be in your report\)](#)

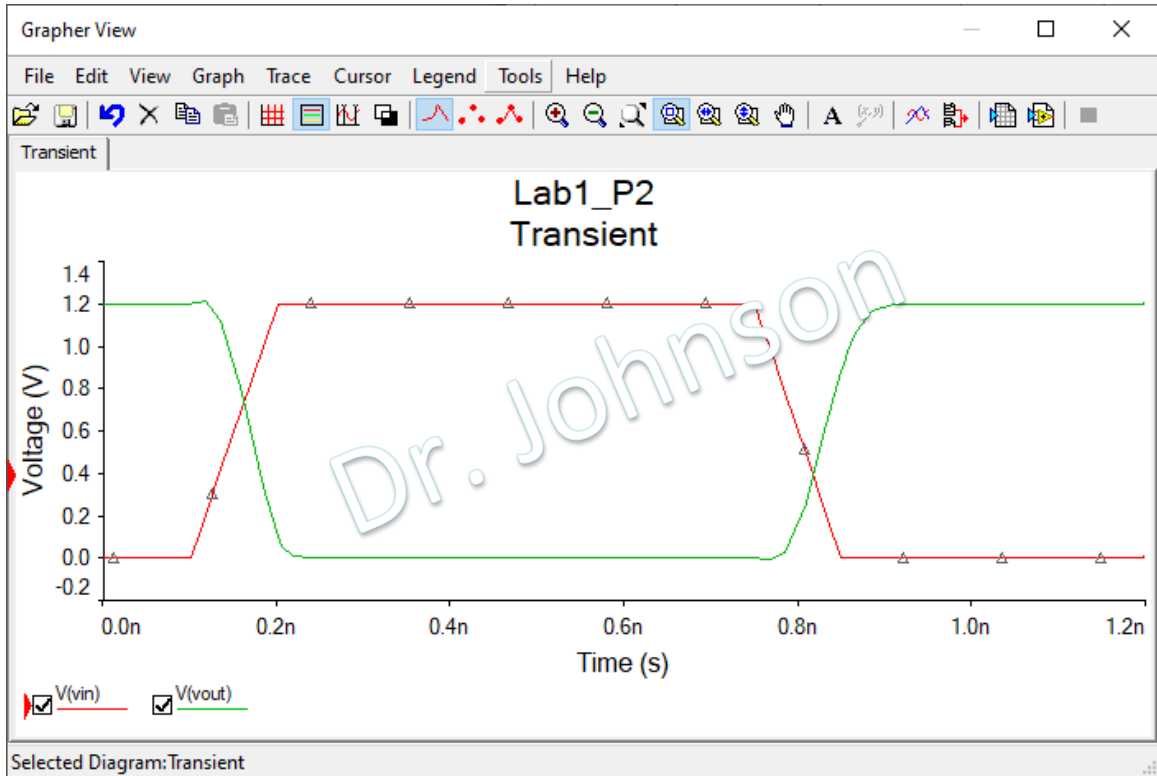
- Part 1 – RC time constant (Simulation) 40%
- Part 2 – Inverter Currents (Simulation) 40%

Lab Report (informal)

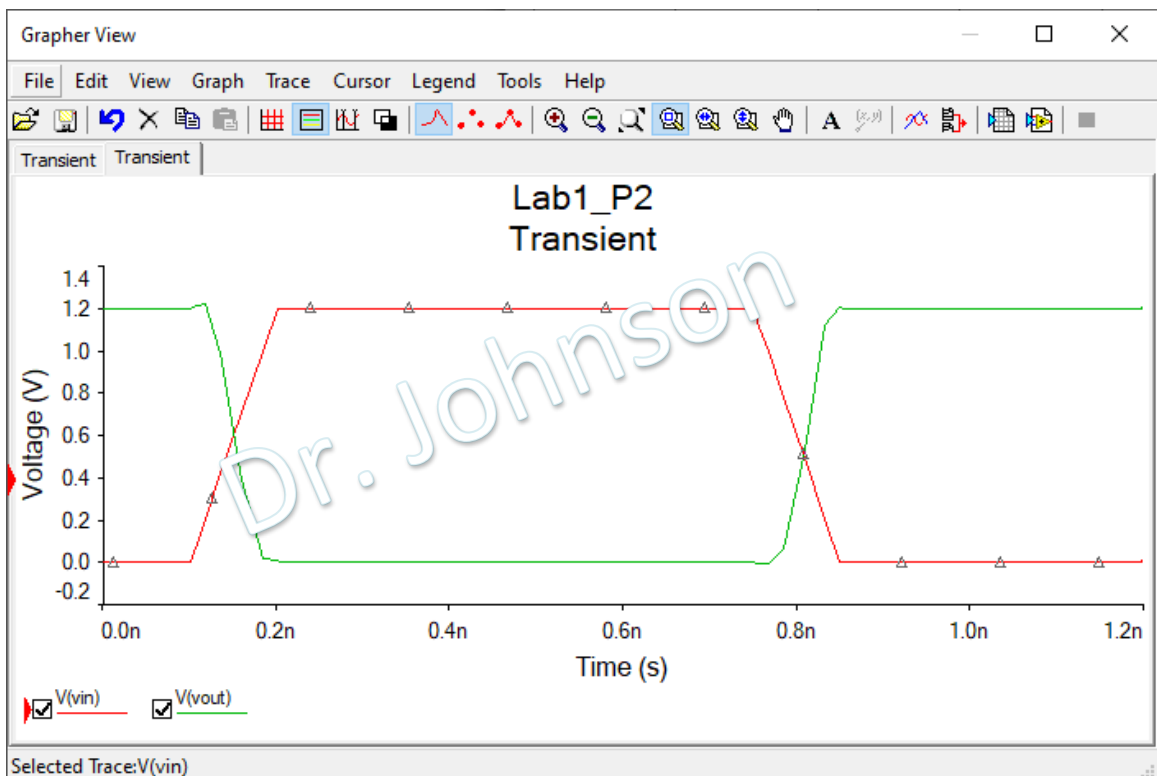
- Due at 4:00 pm, the day of the lab following the second lab – in the box
- Include a properly documented informal lab report. 20%

Part 2 Appendix

- a) Run a transient simulation and plot v_{in} and v_{out} to verify connections.



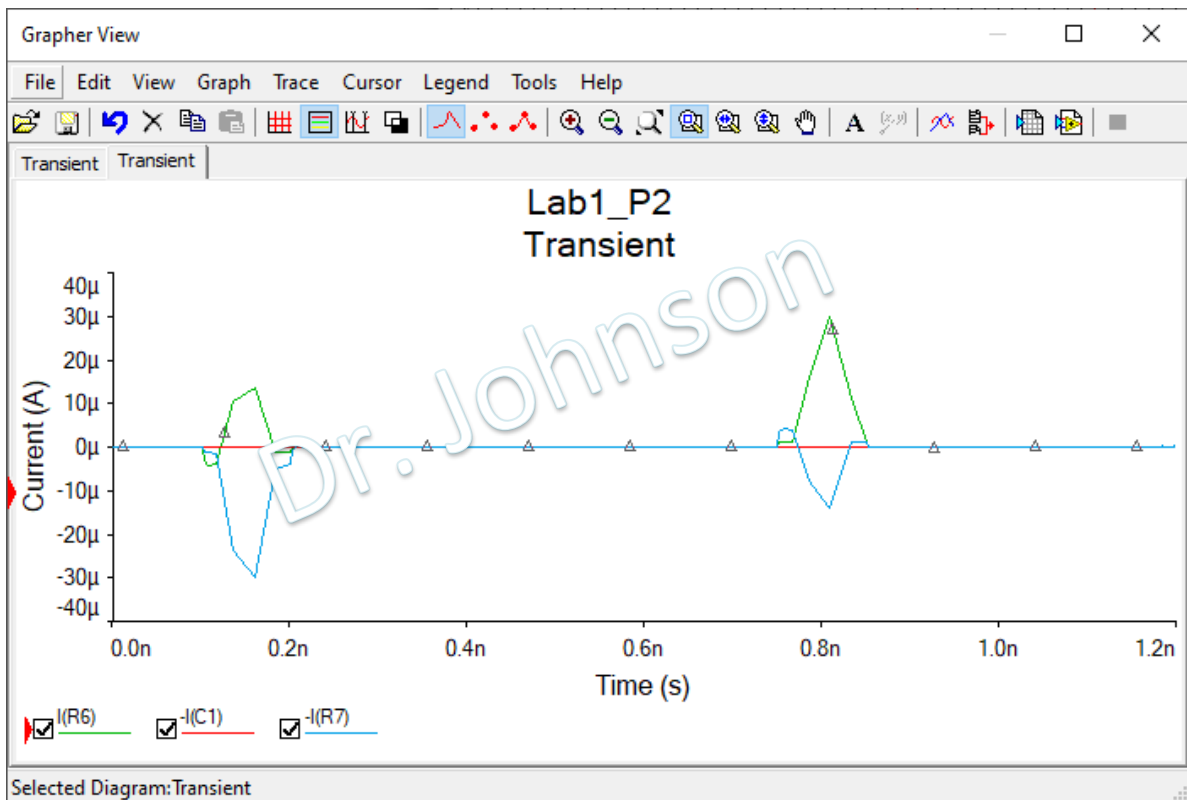
- b) Temporarily **disconnect** the load capacitor and rerun the simulation from part a
Why are the transition delays reduced?



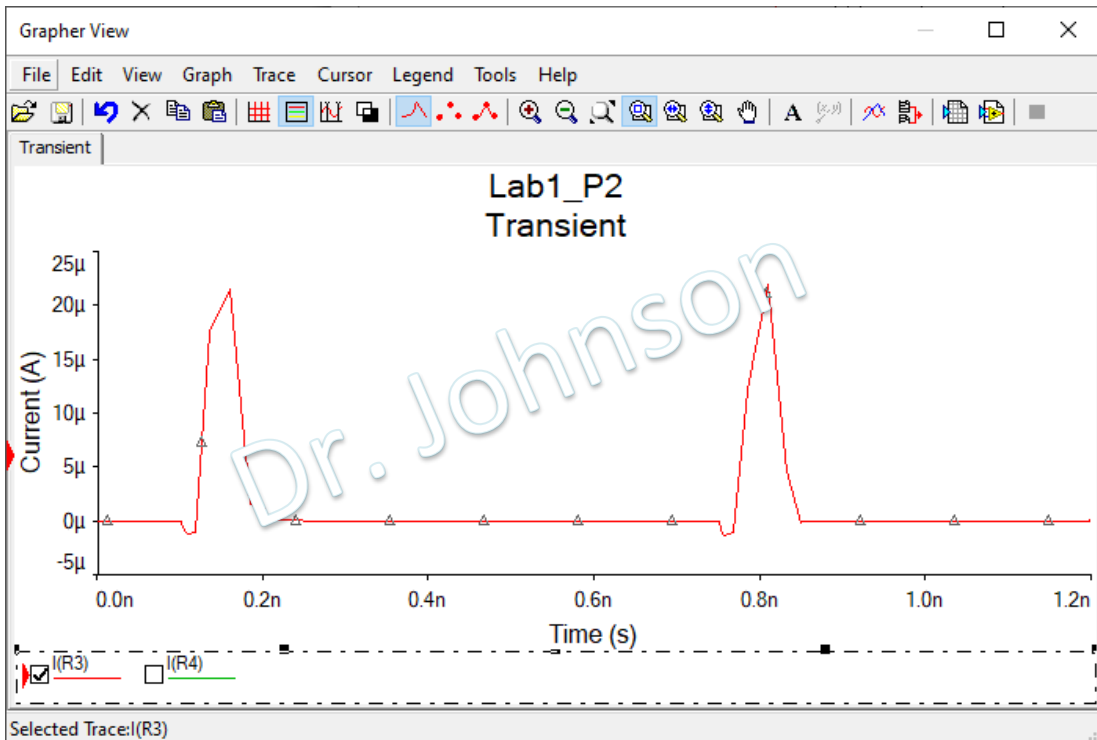
- c) **Reconnect** the load capacitor. Run a transient simulation and plot $-I(C)$, $I(R6)$, $-I(R7)$
Note: The currents do not sum to 0, **where is the missing current going?**



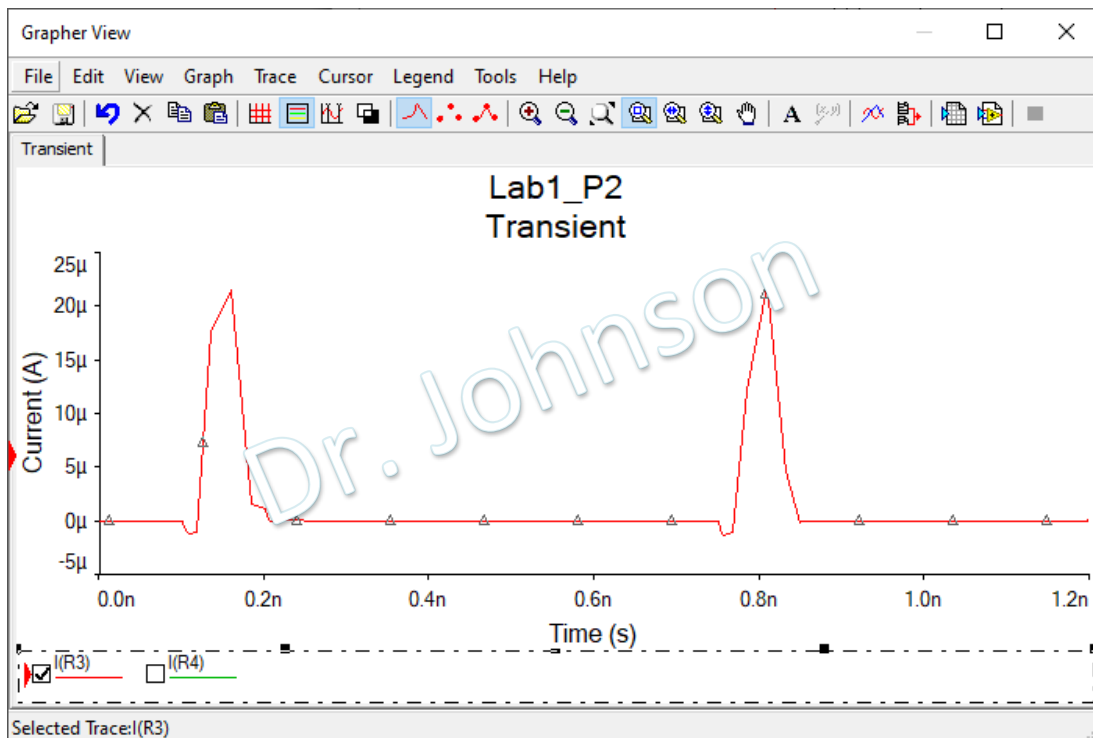
- d) **Disconnect** the load capacitor and rerun the simulation from part c
Note: The currents do not sum to 0, **where is the missing current going?**



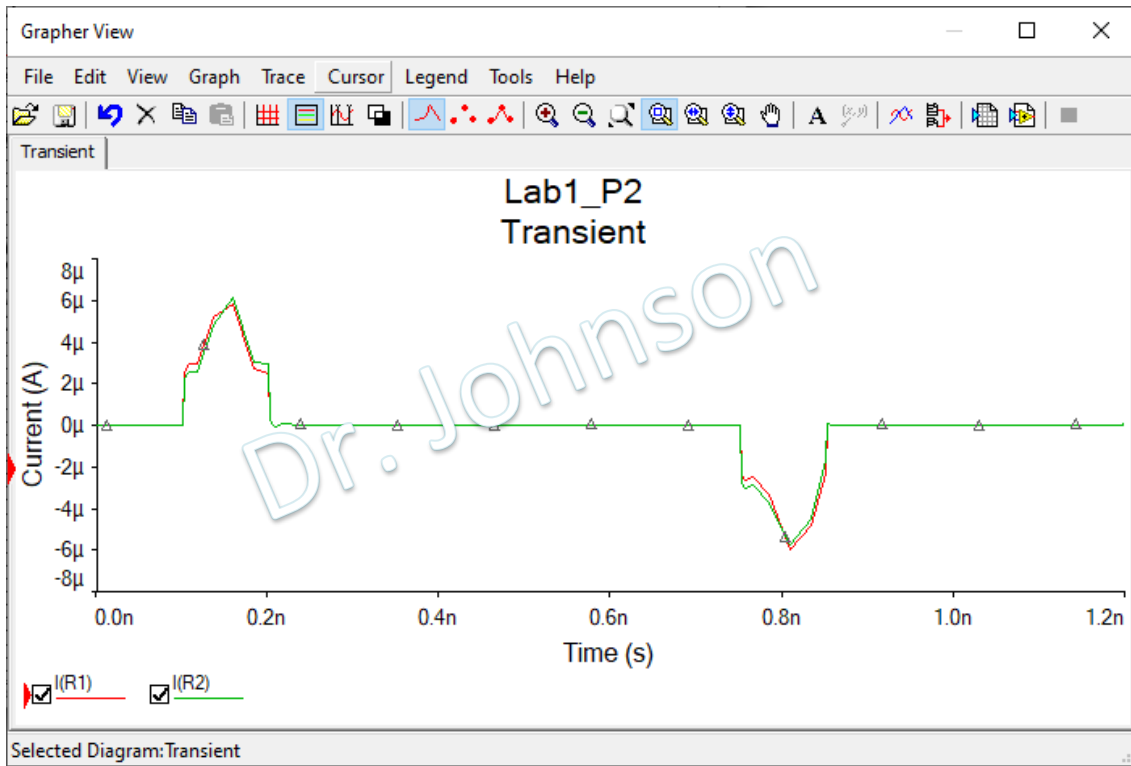
- e) With the load capacitor disconnected plot $I(R3)$ or $I(R4)$.
Zoom in on the small spike near 0.15ns.
This is the shoot-through current in the inverter.



- f) With the load capacitor disconnected plot $I(R3)$ or $I(R4)$.
Zoom in on the small spike at 0.8ns.
This is the shoot-through current in the inverter.



- g) With the load capacitor disconnected plot the $I(R1)$ and $I(R2)$
 Note: Though we often think of CMOS gates as having zero input current, there is clearly a significant current here, **why?**



- h) With the load capacitor disconnected, plot the 4 terminal currents for each transistor
 Note: The sum of these should equal 0 for each transistor

